

## HMIC™ PIN Diode SPDT 50 Watt Switch for 0.05 - 6.0 GHz Higher Power Applications

Rev. V5

### Features

- Exceptional Broadband Performance, 0.05 - 6.0 GHz
- Low Loss:  $T_x = 0.33 \text{ dB @ } 2010 \text{ MHz, } 5\text{V} / 20\text{mA}$
- $T_x = 0.38 \text{ dB @ } 3.5 \text{ GHz, } 5\text{V} / 20\text{mA}$
- High Isolation:  $R_x = 44\text{dB @ } 2010 \text{ MHz, } 20\text{mA} / 5\text{V}$
- $R_x = 36\text{dB @ } 3.5 \text{ GHz, } 20\text{mA} / 5\text{V}$
- High  $T_x$  RF Input Power = 50 W C.W. @ 2010MHz
- High Tx RF Input Peak Power > 1000 W
- Suitable for Very High Power TD-SCDMA & WiMAX Applications
- Surface Mount 4mm PQFN Package, RoHS\* Compliant

### Description and Applications

The MA-COM MASW-000834-13560T is a SPDT Broadband, high linearity, common anode, PIN diode T/R switch for 0.05 - 6.0 GHz applications, including WiMAX & WiFi. The device is provided in industry standard 4mm PQFN plastic packaging. This device incorporates a PIN diode die fabricated with M/A-COM's patented Silicon-Glass HMIC™ process. This chip features two silicon pedestals embedded in a low loss, low dispersion glass. The diodes are formed on the top of each pedestal. The topside is fully encapsulated with silicon nitride and has an additional polymer passivation layer. These polymer protective coatings prevent damage and contamination during handling and assembly.

This compact 4mm PQFN package, SPDT switch offers wideband 0.05 - 6.0 GHz performance with excellent isolation to loss ratio for both  $T_x$  and  $R_x$  states. The PIN diode provides exceptional 50 W C.W. power handling and 65 dBm IIP3 at 2010 MHz for maximum switch performance.

### Absolute Maximum Ratings <sup>1</sup>

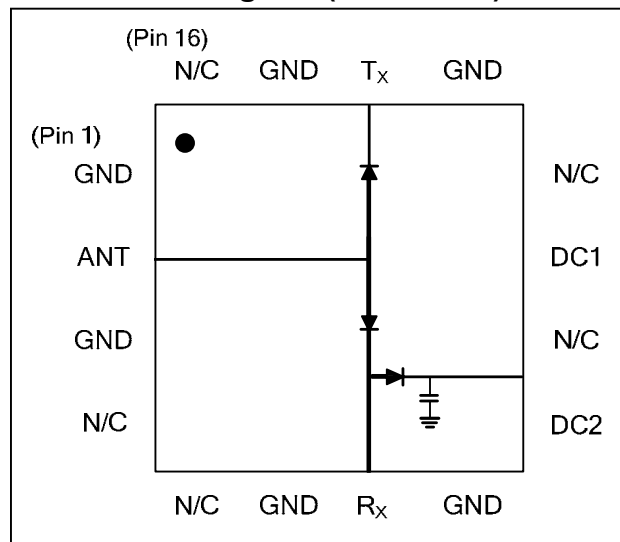
@  $T_A = +25 \text{ °C}$  (unless otherwise specified)

Parameter	Absolute Maximum
Forward Current	100 mA
Reverse Voltage ( RF & D.C. )	-200 V
Operating Temperature	-40 °C to +85 °C
Storage Temperature	-55 °C to +150 °C
Junction Temperature	+175 °C
$T_x$ Incident C.W. Power	50W (47 dBm) <sup>2</sup> @ 2010MHz
$T_x$ Peak Incident Power	>300 W, 5us, 1% duty

1. Exceeding these limits may cause permanent damage.
2. Baseplate Temperature must be controlled to a constant 25°C. See page 7 for derating curve.

\* Restrictions on Hazardous Substances, European Union Directive

### Functional Diagram (TOP VIEW)



### Pin Configuration:

(Center Metal Area is RF, D.C., and Thermal Ground)

Pin	Function	Pin	Function
1	GND	9	DC2
2	ANT	10	N/C
3	GND	11	DC1
4	N/C	12	N/C
5	N/C	13	GND
6	GND	14	TX
7	RX	15	GND
8	GND	16	N/C

### Ordering Information

Part Number	Package
MASW-000834-13560T	Tape and Reel
MASW-000834-001SMB	Sample Board
MADR-008851-0001TB	Sample Board with recommended external Driver & MASW-000834-13560T Switch

### Static Sensitivity

These devices are rated Class 1B Human Body. Proper ESD control techniques should be used when handling these devices.

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## HMIC™ PIN Diode SPDT 50 Watt Switch for 0.05 - 6.0 GHz Higher Power Applications

Rev. V5

### Electrical Specifications at +25°C, Characteristic Impedance, 20mA / 5V, $Z_0 = 50 \Omega$

Parameter	Symbol	20mA / 5V Conditions	Units	Min.	Typ.	Max.
<b>F = 900 MHz</b>						
Insertion Loss, $R_X$	$R_X$ IL	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	0.34	0.56
Insertion Loss, $T_X$	$T_X$ IL	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	0.26	0.445
Isolation, $T_X$ To $R_X$	$R_X$ ISO	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	45.8	52.1	—
Isolation, $R_X$ To $T_X$	$T_X$ ISO	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	21.7	27.1	—
<b>F = 1800 MHz</b>						
Insertion Loss, $R_X$	$R_X$ IL	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	0.40	0.72
Insertion Loss, $T_X$	$T_X$ IL	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	0.32	0.49
Isolation, $T_X$ To $R_X$	$R_X$ ISO	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	43.7	48.9	—
Isolation, $R_X$ To $T_X$	$T_X$ ISO	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	18.4	21.4	—
<b>F = 2010 MHz</b>						
Insertion Loss, $R_X$	$R_X$ IL	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	0.42	0.75
Insertion Loss, $T_X$	$T_X$ IL	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	0.33	0.5
Isolation, $T_X$ To $R_X$	$R_X$ ISO	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	43.2	44.6	—
Isolation, $R_X$ To $T_X$	$T_X$ ISO	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	17.7	19.9	—
Input Return Loss, $T_X$	$T_X$ RL	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	32.1	—
Input Return Loss, $R_X$	$R_X$ RL	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	24.2	—

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Parameter	Symbol	20mA / 5V Conditions	Units	Min.	Typ.	Max.
<b>F = 2.3-2.7 GHz</b>						
Insertion Loss, $R_X$	$R_X$ IL	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	0.46	0.84
Insertion Loss, $T_X$	$T_X$ IL	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	0.35	0.525
Isolation, $T_X$ To $R_X$	$R_X$ ISO	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	40.2	41.2	—
Isolation, $R_X$ To $T_X$	$T_X$ ISO	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	16.2	18.6	—
Input Return Loss, $T_X$	$T_X$ RL	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	30.5	—
Input Return Loss, $R_X$	$R_X$ RL	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	22.9	—
<b>F = 3.3-3.8 GHz</b>						
Insertion Loss, $R_X$	$R_X$ IL	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	0.56	1.0
Insertion Loss, $T_X$	$T_X$ IL	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	0.38	0.575
Isolation, $T_X$ To $R_X$	$R_X$ ISO	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	33.7	35.9	—
Isolation, $R_X$ To $T_X$	$T_X$ ISO	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	13.6	16.1	—
Input Return Loss, $T_X$	$T_X$ RL	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	27.4	—
Input Return Loss, $R_X$	$R_X$ RL	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	21.9	—
<b>F = 4.9-5.9 GHz</b>						
Insertion Loss, $R_X$	$R_X$ IL	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	0.78	—
Insertion Loss, $T_X$	$T_X$ IL	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	0.52	—
Isolation, $T_X$ To $R_X$	$R_X$ ISO	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	26.4	—
Isolation, $R_X$ To $T_X$	$T_X$ ISO	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	11.8	—
Input Return Loss, $T_X$	$T_X$ RL	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	20.3	—
Input Return Loss, $R_X$	$R_X$ RL	See Bias Table 1, pg. 10, Pinc= 0 dBm	dB	—	24.2	—

**Electrical Specifications at +25°C, Characteristic Impedance, 50mA / 25V, Z<sub>0</sub> = 50 Ω**

Parameter	Symbol	50mA / 25V Conditions	Units	Min.	Typ.	Max.
<b>F = 900 MHz</b>						
Insertion Loss, R <sub>X</sub>	R <sub>X</sub> IL	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	0.27	—
Insertion Loss, T <sub>X</sub>	T <sub>X</sub> IL	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	0.22	—
Isolation, T <sub>X</sub> To R <sub>X</sub>	R <sub>X</sub> ISO	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	53.3	—
Isolation, R <sub>X</sub> To T <sub>X</sub>	T <sub>X</sub> ISO	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	27.4	—
<b>F = 1800 MHz</b>						
Insertion Loss, R <sub>X</sub>	R <sub>X</sub> IL	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	0.32	—
Insertion Loss, T <sub>X</sub>	T <sub>X</sub> IL	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	0.27	—
Isolation, T <sub>X</sub> To R <sub>X</sub>	R <sub>X</sub> ISO	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	50.2	—
Isolation, R <sub>X</sub> To T <sub>X</sub>	T <sub>X</sub> ISO	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	21.6	—
<b>F = 2010 MHz</b>						
Insertion Loss, R <sub>X</sub>	R <sub>X</sub> IL	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	0.34	—
Insertion Loss, T <sub>X</sub>	T <sub>X</sub> IL	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	0.28	—
Isolation, T <sub>X</sub> To R <sub>X</sub>	R <sub>X</sub> ISO	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	45.5	—
Isolation, R <sub>X</sub> To T <sub>X</sub>	T <sub>X</sub> ISO	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	20.1	—
Input Return Loss, T <sub>X</sub>	T <sub>X</sub> RL	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	33.1	—
Input Return Loss, R <sub>X</sub>	R <sub>X</sub> RL	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	24.1	—

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Rev. V5

### Electrical Specifications at +25°C, Characteristic Impedance, 50mA / 25V, $Z_0 = 50 \Omega$

Parameter	Symbol	50mA / 25V Conditions	Units	Min.	Typ.	Max.
<b>F = 2.3-2.7 GHz</b>						
Insertion Loss, $R_X$	$R_X$ IL	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	0.38	—
Insertion Loss, $T_X$	$T_X$ IL	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	0.30	—
Isolation, $T_X$ To $R_X$	$R_X$ ISO	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	41.8	—
Isolation, $R_X$ To $T_X$	$T_X$ ISO	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	18.7	—
Input Return Loss, $T_X$	$T_X$ RL	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	31.3	—
Input Return Loss, $R_X$	$R_X$ RL	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	22.8	—
<b>F = 3.3-3.8 GHz</b>						
Insertion Loss, $R_X$	$R_X$ IL	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	0.47	—
Insertion Loss, $T_X$	$T_X$ IL	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	0.33	—
Isolation, $T_X$ To $R_X$	$R_X$ ISO	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	36.2	—
Isolation, $R_X$ To $T_X$	$T_X$ ISO	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	16.2	—
Input Return Loss, $T_X$	$T_X$ RL	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	28.0	—
Input Return Loss, $R_X$	$R_X$ RL	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	21.8	—
<b>F = 4.9-5.9 GHz</b>						
Insertion Loss, $R_X$	$R_X$ IL	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	0.72	—
Insertion Loss, $T_X$	$T_X$ IL	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	0.48	—
Isolation, $T_X$ To $R_X$	$R_X$ ISO	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	26.6	—
Isolation, $R_X$ To $T_X$	$T_X$ ISO	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	11.8	—
Input Return Loss, $T_X$	$T_X$ RL	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	20.5	—
Input Return Loss, $R_X$	$R_X$ RL	See Bias Table 2, pg. 10, Pinc= 0 dBm	dB	—	24.2	—

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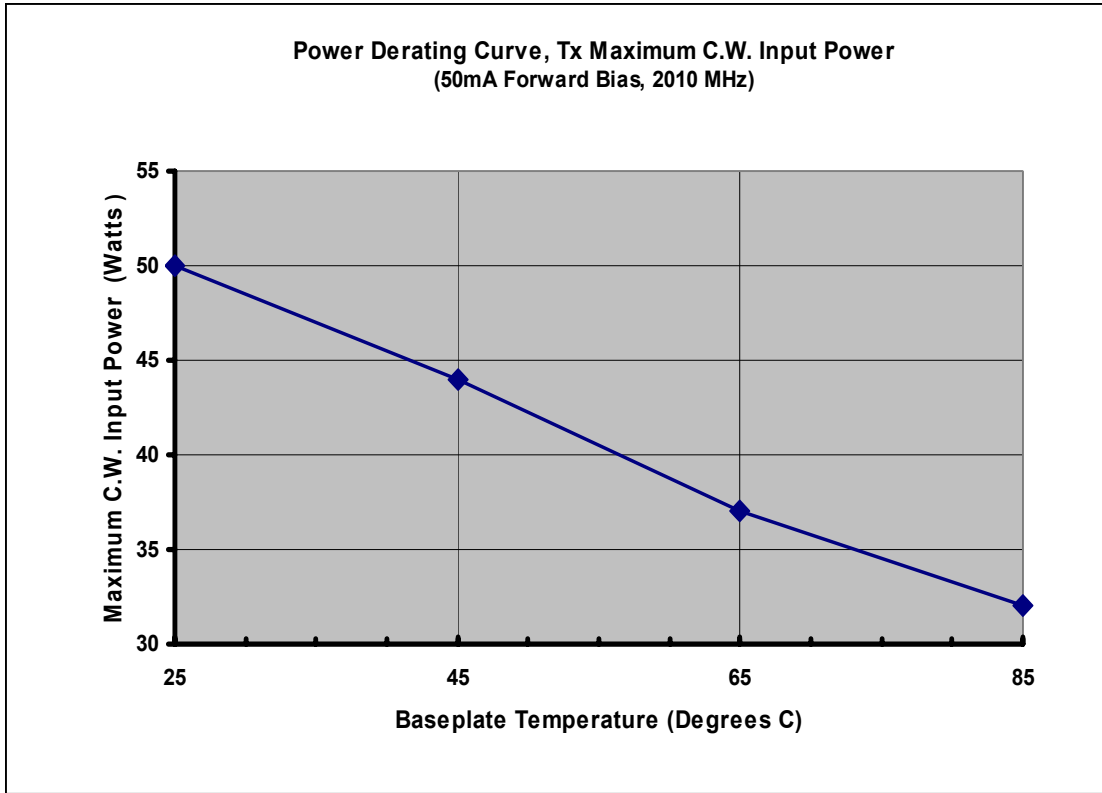
Rev. V5

### Electrical Specifications at +25°C, Characteristic Impedance, 50mA / 25V, $Z_0 = 50 \Omega$

Parameter	Symbol	50mA / 25V Conditions	Units	Min.	Typ.	Max.
$T_X$ Input P1dB <sup>2</sup>	$T_X$ P1dB	2010 MHz, $T_X$ to Antenna	dBm	—	>45.5	—
$T_X$ 2 <sup>nd</sup> Harmonic	$T_X$ 2F <sub>0</sub>	2010 MHz, Pin = + 30 dBm	dBc	—	80	—
$T_X$ 3 <sup>rd</sup> Harmonic	$T_X$ 3F <sub>0</sub>	2010 MHz, Pin = + 30 dBm	dBc	—	95	—
$T_X$ Input Third Order Intercept Point	$T_X$ IIP3	Pi= +10dBm, F1 = 2010 MHz, F2 = 2020 MHz	dBm	—	>64	—
$T_X$ C.W. Input Power <sup>2</sup>	$T_X$ Pinc	F = 2010 MHz	dBm W	—	—	47 50
$R_X$ C.W. Input Power	$R_X$ Pinc	F = 2010 MHz	dBm W	—	—	41.5 14
$T_X$ RF Switching Speed	$t_{RF}$	F = 2010 MHz ( 10-90% RF Voltage) 1MHz Rep Rate in Modulating Mode	ns	—	200	—

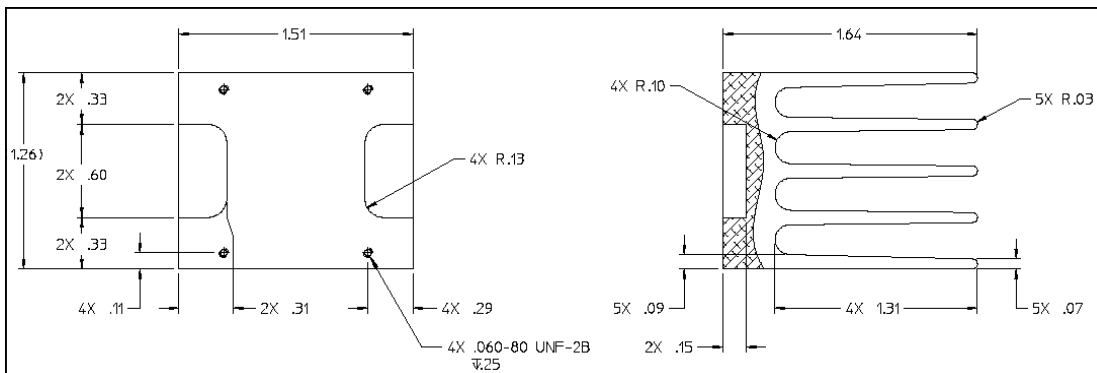
Parameter	Symbol	50mA / 25V Conditions	Units	Min.	Typ.	Max.
$T_X$ Input P1dB	$T_X$ IP1dB	3.5 GHz, $T_X$ to Antenna	dBm	—	>45	—
$T_X$ 2 <sup>nd</sup> Harmonic	$T_X$ 2F <sub>0</sub>	3.5 GHz, Pin = + 30 dBm	dBc	—	88	—
$T_X$ 3 <sup>rd</sup> Harmonic	$T_X$ 3F <sub>0</sub>	3.5 GHz, Pin = + 30 dBm	dBc	—	105	—
$T_X$ Input Third Order Intercept Point	$T_X$ IIP3	Pi= +10dBm, F1 = 3.500 GHz, F2 = 3.510 GHz	dBm	—	>64	—
$R_X$ C.W. Input Power	$R_X$ Pinc	F = 3.5 GHz	dBm W	—	—	40.5 11
$T_X$ RF Switching Speed	$t_{RF}$	F = 3.5 GHz ( 10-90% RF Voltage) 1MHz Rep Rate in Modulating Mode	ns	—	200	—

**Electrical Specifications at +25°C, Characteristic Impedance, 50mA / 25V,  $Z_0 = 50 \Omega$**



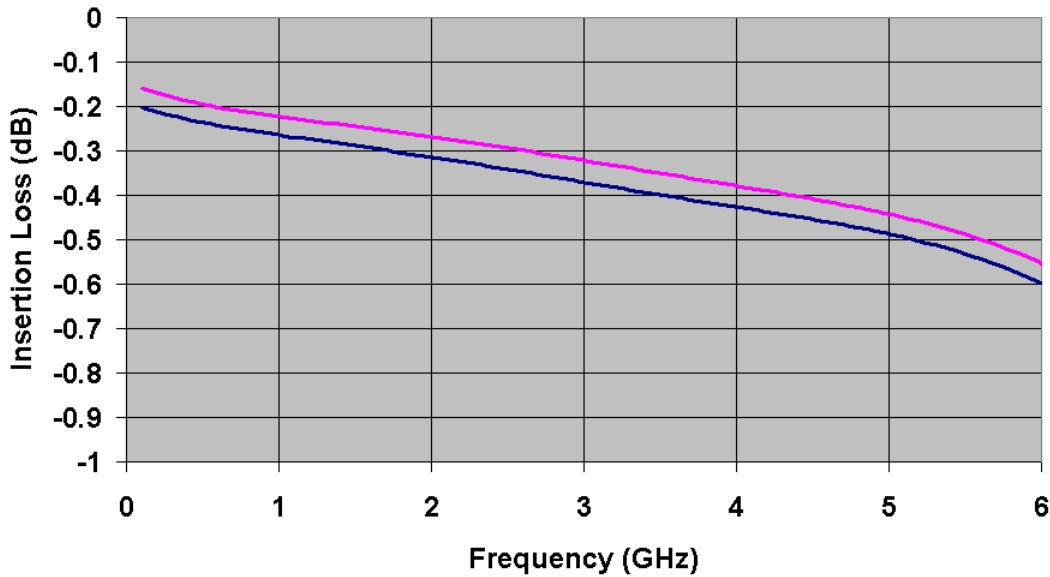
Note that this part must be held to a constant baseplate temperature to achieve the power handling results specified above. Adding a heatsink to the baseplate will improve performance to values greater than shown here. The increase in maximum input power from using a heatsink depends on the specific heatsink design.

With a sample board mounted onto a heatsink of dimensions and fins shown below, this switch can handle up to 35 Watts C.W. of incident power.

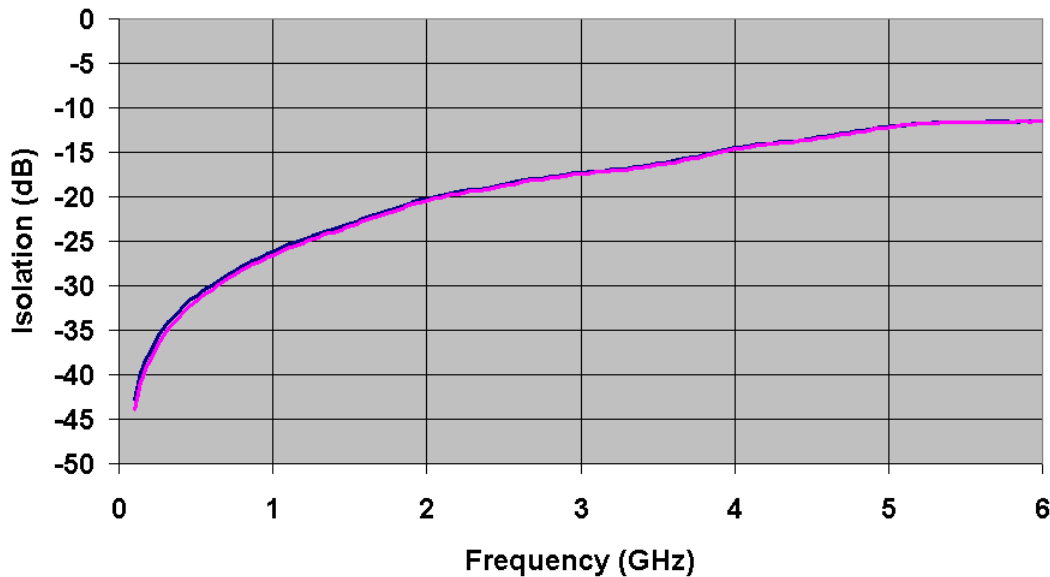


## T<sub>x</sub> Performance Curves at +25°C, Characteristic Impedance, Z<sub>0</sub> = 50 Ω

**Tx Insertion Loss**  
20mA & 50mA Forward Bias

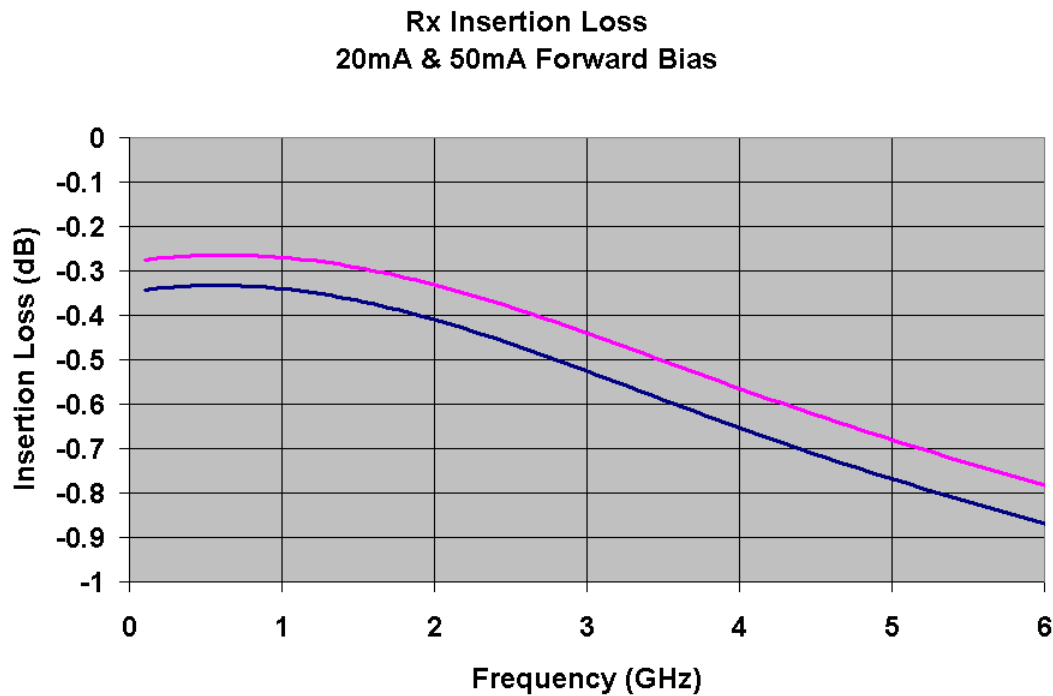
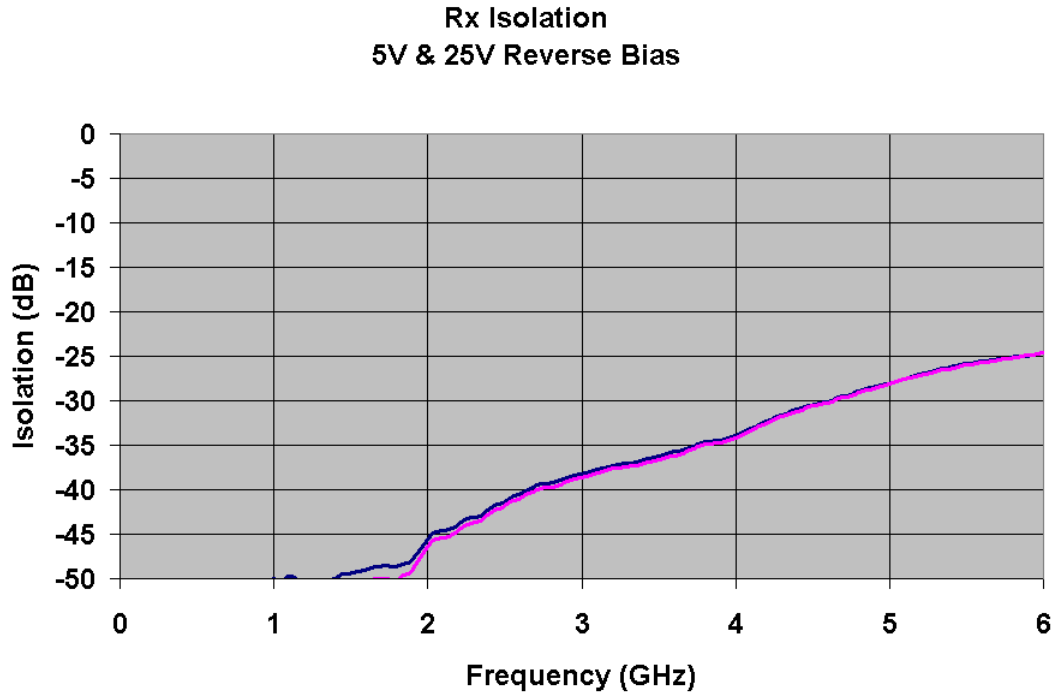


**Tx Isolation**  
5V & 25V Reverse Bias

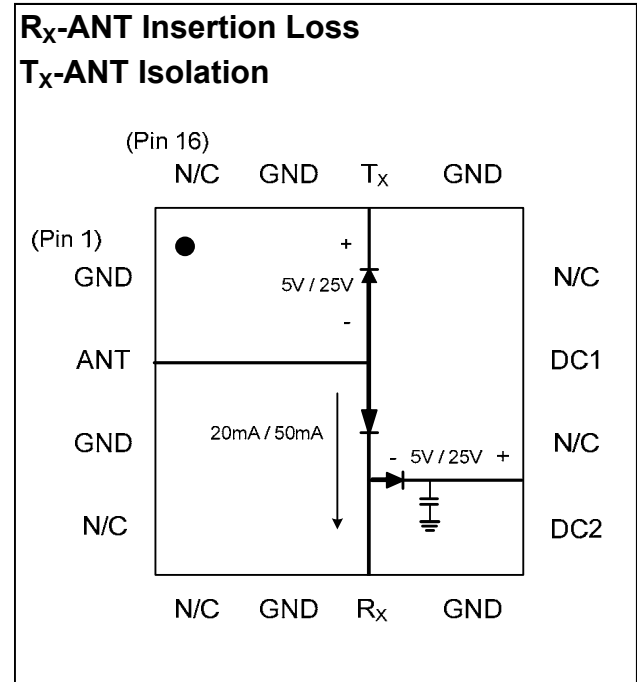
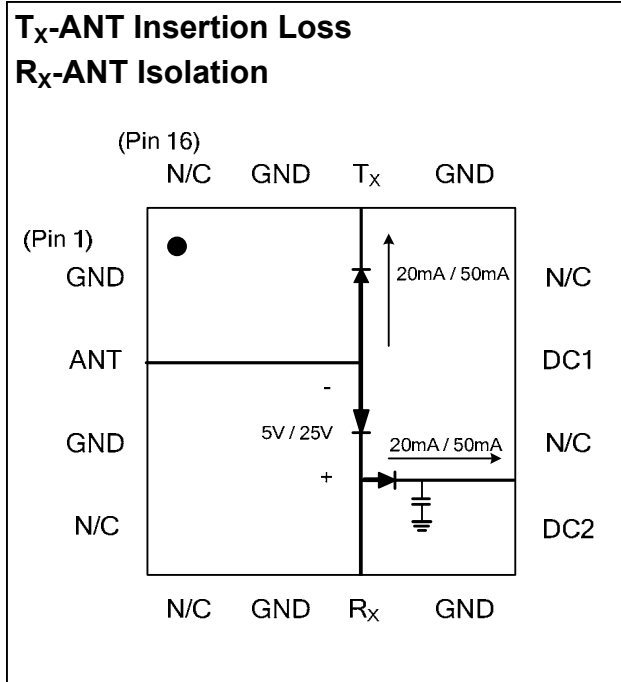




## R<sub>x</sub> Performance Curves at +25°C, Characteristic Impedance, Z<sub>0</sub> = 50 Ω



## Bias Diagrams & Tables



Bias Table 1	T <sub>x</sub>	R <sub>x</sub>	DC2	ANT
Pin	Pin 14	Pin 7	Pin 9	Pin 2
T <sub>x</sub> -ANT Isolation	+5V, 0 mA	-20 mA	+5V, 0 mA	0V
T <sub>x</sub> -ANT Insertion Loss	-20 mA	+5V, 0 mA	-20 mA	0V
R <sub>x</sub> -ANT Isolation	-20 mA	+5V, 0 mA	-20 mA	0V
R <sub>x</sub> -ANT Insertion Loss	+5V, 0 mA	-20 mA	+5V, 0 mA	0V

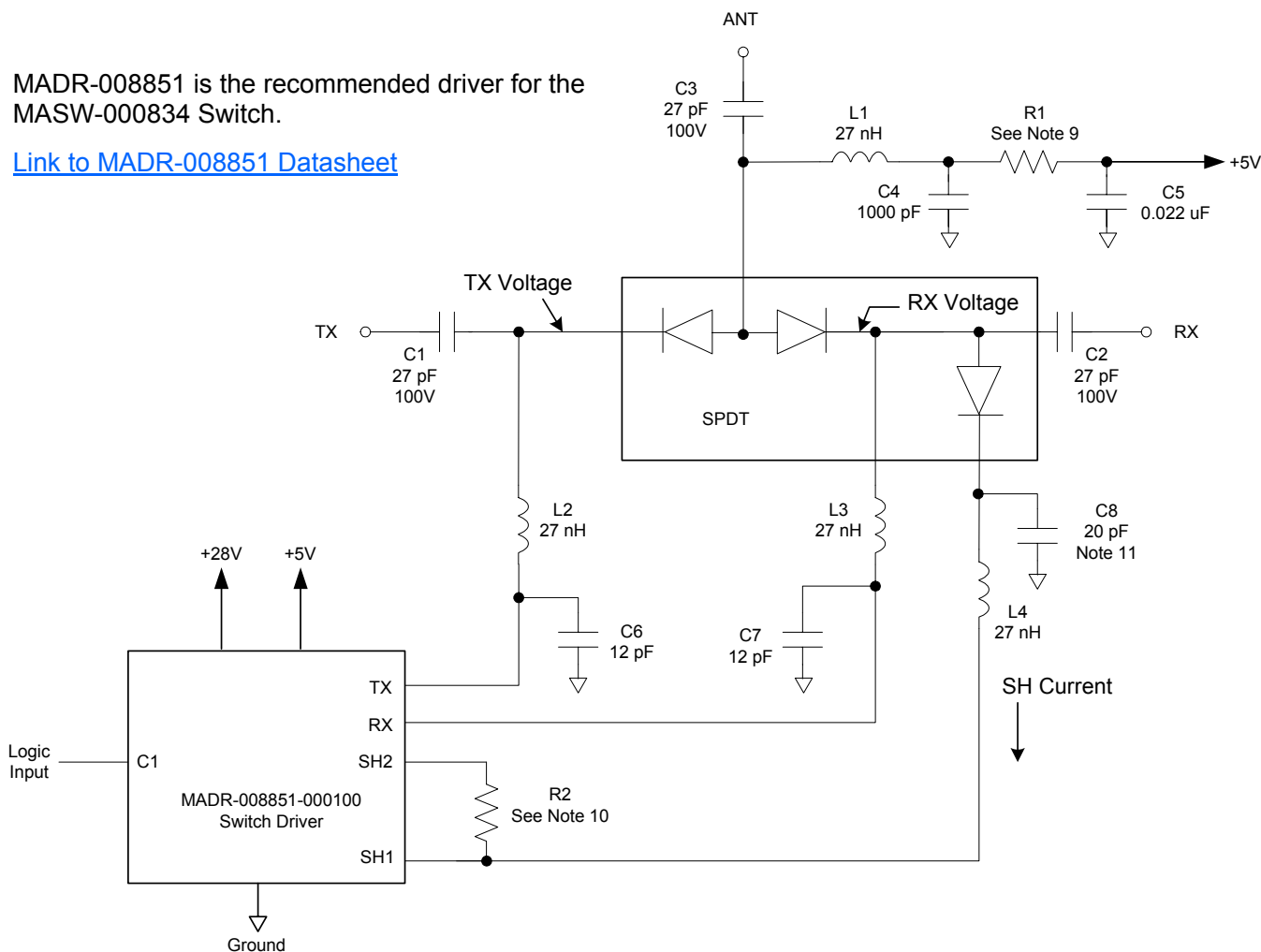
Bias Table 2	T <sub>x</sub>	R <sub>x</sub>	DC2	ANT
Pin	Pin 14	Pin 7	Pin 9	Pin 2
T <sub>x</sub> -ANT Isolation	+25V, 0 mA	-50 mA	+25V, 0 mA	0V
T <sub>x</sub> -ANT Insertion Loss	-50 mA	+25V, 0 mA	-50 mA	0V
R <sub>x</sub> -ANT Isolation	-50 mA	+25V, 0 mA	-50 mA	0V
R <sub>x</sub> -ANT Insertion Loss	+25V, 0 mA	-50 mA	+25V, 0 mA	0V



## MASW-000834 and Recommended Driver with +5V & +28V DC Power

MADR-008851 is the recommended driver for the MASW-000834 Switch.

[Link to MADR-008851 Datasheet](#)



8. Forward Bias Diode Voltage:  $\Delta V_f$  is  $\sim 0.9V @ 22 \text{ mA}$ ;  $\Delta V_f$  is  $\sim 1.0V @ 35 \text{ mA}$
9. R1 is calculated by  $(V_{cc}-1.5V)/I_{series}$ , where  $I_{series}$  is the desired bias current for the series diodes. For 21 mA load current,  $R1 = 165 \Omega @ VCC = 5.0V$  and  $82 \Omega @ VCC = 3.3V$ . For 32 mA load current,  $R1 = 110 \Omega @ VCC = 5.0V$  and  $56 \Omega @ VCC = 3.3V$ .
10. R2 is calculated by  $(V_{dd}-1V)/I_{shunt}$ , where  $I_{shunt}$  is the desired forward bias current for the shunt diode. The power dissipation is calculated by  $I_{shunt} \times 27V$ . For 20 mA of  $I_{shunt}$ , R2 should use a 2511, 1W, 1.3k ohm resistor.
11. C8 is already built-in for M/A-COM MASW-000834-13560T switch.
12. The voltage at the common anode will be approximately 1.5V.
13. The current in through the back-biased diodes will be the leakage current for the diodes
14. C1-C5, L1-L4, R1, R2, and the switch are discrete components that should be installed on the user's board. It is recommended that Coilcraft 0603CS-27NXJLW or equivalent be used for L1-L4 at 2 GHz (values may vary based on the frequency).
15. There are 33 pF bypass capacitors included in the driver for the RX, TX, and SH1 ports. There are cases, especially at higher frequencies, where the optional 12 pF bypass capacitors (C6 and C7) that are shown on the schematic are needed.